

PATENT

81784.0241

Express Mail Label No. EL713625653US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Masayuki KOGA et al.

Serial No: (Not Assigned: Parent 09/148,854)

Filed: August 8, 2001

For: DISPLAY DEVICE AND
SEMICONDUCTOR DEVICE
HAVING LASER ANNEALED
SEMICONDUCTOR ELEMENTS

Art Unit: Not Assigned

Examiner: Not Assigned

PRELIMINARY AMENDMENT

Box PATENT APPLICATION

Commissioner for Patents

Washington, D.C. 20231

Dear Sir:

Prior to examining the above-referenced application, please amend the above-referenced application as follows:

IN THE CLAIMS:

Please cancel claim 1 without prejudice.

Please replace the text of claim 10 with the following text:

10. (Amended) A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements each has a plurality of channel areas (a) which are formed in a semiconductor layer subjected to laser annealing respectively, and (b) which are the same conductive type channel areas, and the plurality of channel areas are electrically connected to each other and arranged separately and in different directions to each other.

Please add the following new claims 13-15:

13. (New) A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements each has a plurality of channel areas which are formed in a semiconductor layer subjected to laser annealing respectively, and which are the same conductive type channel areas, and the plurality of channel areas are electrically connected to each other and arranged separately and in parallel to each other.

14. (New) The semiconductor device according to claim 13, wherein a distance between the plurality of channel areas is determined that a virtual channel width containing a separated space is larger than a width of a defectively processed area caused in the semiconductor layer during the laser annealing.

15. (New) The semiconductor device according to claim 13, wherein the laser annealing is performed to polycrystallize an amorphous semiconductor layer in order to obtain a polycrystalline semiconductor layer.

REMARKS:

This is a preliminary amendment of the above-referenced application. Applicant cancels claim 1 of the present application and adds new claims 13-15 to the present application. Applicant further amends claim 10 of the present application; marked up version of the amended claim is attached hereto pursuant to 37 C.F.R. § 1.121(c)(ii). Pursuant to this amendment, claims 10-15 are pending. Applicant respectfully submits that all pending claims distinguish over the art of record and are in condition for allowance.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at the Los Angeles, California telephone number (213) 337-6870 to discuss the steps necessary for placing the application in condition for allowance.

If there are any fees due in connection with the filing of this response, please charge the fees to our Deposit Account No. 50-1314.

Respectfully submitted,

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By: 

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Version with markings to show changes made:

10. (Amended) A semiconductor device having a plurality of semiconductor elements on a substrate, wherein some or all of the semiconductor elements [have] each has a plurality of channel areas (a) which are formed in a semiconductor layer subjected to laser annealing respectively, and (b) which are the same conductive type channel areas, and the plurality of channel areas are electrically connected [in parallel] to each other and arranged separately [and/or arranged] and in different directions to each other.